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## A-9903 PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Lars Ivar SAMUELSON et al.

Appln. No.: 10/751,943 Group Art Unit: 2878

Filed: January 7, 2004

For: PROBE STRUCTURES INCORPORATING NANOWHISKERS,

PRODUCTION METHODS THEREOF, AND METHODS OF FORMING

NANOWHISKERS

## INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any assertion as to materiality or prior art effect, the documents listed on the attached Form PTO-1449 are hereby cited.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit any overpayment to that Account. If any extension of time is required in connection with the filing of this paper and has not been requested separately, such extension is hereby requested.

Respectfully submitted,

Reg. No. 31,56

MWS: lmb

Miles & Stockbridge P.C. 1751 Pinnacle Drive, Suite 500 McLean, Virginia 22102-3833 (703) 903-9000

June 30, 2005

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